NSN 5961-01-036-6899

Transistor - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-036-6899 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.450 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact-darlington connected Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case: Internal Junction Configuration:** Npn **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 40.0 breakdown voltage, collector-to-base, emitter open and 5.0 emitter to base voltage, static, collector open and 40.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 10.00 amperes source cutoff current and 250.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 100.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

Demilitarization: Yes - demil/mli